

IN THE CLAIMS

Please amend the claims as follows.

For the Examiner's convenience, a list of all claims is included below.

1. (Currently Amended) A method ~~for sequencing a developer process to reduce wafer pattern defects~~, comprising:

dispensing a first quantity of a substantially inert material onto a wafer surface to form a layer of substantially inert material ~~prior to dispensing a developer fluid, wherein the substantially inert material is dispensed through a selected multi-dispense nozzle;~~

dispensing ~~the~~ a first charge of developer fluid onto the surface of the wafer, such that a momentum imparted by the first charge of developer fluid to a micro-structure on the wafer surface is reduced by the layer of substantially inert material; ~~through the same multi-dispense nozzle onto the layer of inert material while spinning the wafer surface substantially simultaneously to induce a flow of the developer fluid across a portion of the wafer surface toward the outer edge of the wafer surface;~~

allowing ~~the~~ at least a portion of developer fluid of the first charge of developer fluid to puddle on the wafer surface for a predetermined dwell time to permit substantial completion of a developing chemical reaction to occur, a non-uniformity of the developing chemical reaction reduced by a diffusion of the puddling developing developer fluid through the inert material;

dispensing a ~~fresh~~ second charge of ~~the~~ developer fluid ~~in addition to the previously dispensed developer fluid through the same multi-dispense nozzle~~ onto the surface of the wafer;
and

dispensing ~~another~~ second quantity of substantially inert material ~~through the same multi-dispense nozzle to rinse the wafer surface~~ onto the wafer surface.

2-3 (Cancelled)

4. (Currently Amended) The method of claim 1 further comprising the step of:
dispensing ~~another~~ a quantity of substantially inert material ~~over a~~ onto the wafer surface subsequent to dispensing the ~~fresh~~ second charge of developer fluid while rotating the wafer surface.
5. (Previously presented) The method ~~as recited in~~ of claim 4 further comprising the step of:
spinning the wafer surface to achieve a selected level of dryness.
- 6 –11 (Cancelled)
12. (New) The method of claim 1 wherein the substantially inert material comprises deionized water.
13. (New) The method of claim 1 wherein the developing chemical reaction is controlled by a flux resulting from the diffusion of the developing fluid through the inert material toward the surface of the wafer.
14. (New) The method of claim 1 wherein a variation of a pH of the developer fluid compared to a pH of the substantially inert material is reduced throughout a duration of the developing chemical reaction.
15. (New) The method of claim 14 wherein the reduced variation of the pH of the developer fluid compared to the pH of the substantially inert material results in a reduction of developer reactants precipitating on the surface of the wafer.